

ABSTRACT

The invention relates to a vertical transistor and an oxidation process that achieves a substantially curvilinear recess bottom. The recess serves as the gate receptacle that may facilitate a more uniform gate oxide layer. One embodiment relates
5 to a storage cell that is disposed in the recess along with an electrode. Another embodiment relates to a system that includes the vertical transistor or the vertical storage cell.

"Express Mail" mailing label number: EL873860577US

Date of Deposit: August 30, 2001

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to the Commissioner for Patents, Box Patent Application, Washington, D.C. 20231.